PESD5V0S1BLD

Low capacitance bidirectional ESD protection diode

Rev. 1 — 12 October 2010   **Product data sheet**

1. Product profile

1.1 General description

Low capacitance bidirectional ElectroStatic Discharge (ESD) protection diode designed to protect one signal line from the damage caused by ESD and other transients. The device is housed in a SOD882D leadless ultra small Surface-Mounted Device (SMD) plastic package with visible and solderable side pads.

1.2 Features and benefits

- Bidirectional ESD protection of one line
- Ultra small SMD plastic package
- Solderable side pads
- Package height typ. 0.37 mm
- Low clamping voltage: V_{CL} = 14 V
- AEC-Q101 qualified
- ESD protection up to 30 kV
- IEC 61000-4-2; level 4 (ESD)
- IEC 61000-4-5 (surge); I_{PP} = 12 A
- Max. peak pulse power: P_{PP} = 130 W
- Ultra low leakage current: I_{RM} = 5 nA

1.3 Applications

- Computers and peripherals
- Audio and video equipment
- Cellular handsets and accessories
- Communication systems
- Portable electronics

1.4 Quick reference data

Table 1. Quick reference data
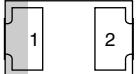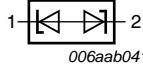
T_{amb} = 25 ℃ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Per diode						
V_{RWM}	reverse standoff voltage		-	-	5.0	V
C_d	diode capacitance	f = 1 MHz; V_R = 0 V	-	35	45	pF

2.   Pinning information

Table 2.   Pinning

Pin	Description	Simplified outline	Graphic symbol
1	cathode 1 [1]		
2	cathode 2	Transparent top view	*006aab041*

[1]   The marking bar indicates cathode 1.

3.   Ordering information

Table 3.   Ordering information

Type number	Package		Version
	Name	**Description**	
PESD5V0S1BLD	-	leadless ultra small plastic package; 2 terminals; body $1.0 \times 0.6 \times 0.4$ mm	SOD882D

4.   Marking

Table 4.   Marking codes

Type number	Marking code[1]
PESD5V0S1BLD	1100 0000

[1]   For SOD882D binary marking code description, see Figure 1.

4.1 Binary marking code description

CATHODE BAR

READING DIRECTION

VENDOR CODE

READING EXAMPLE:

0111
1011

MARKING CODE (EXAMPLE)

READING DIRECTION

006aac477

Fig 1.   SOD882D binary marking code description
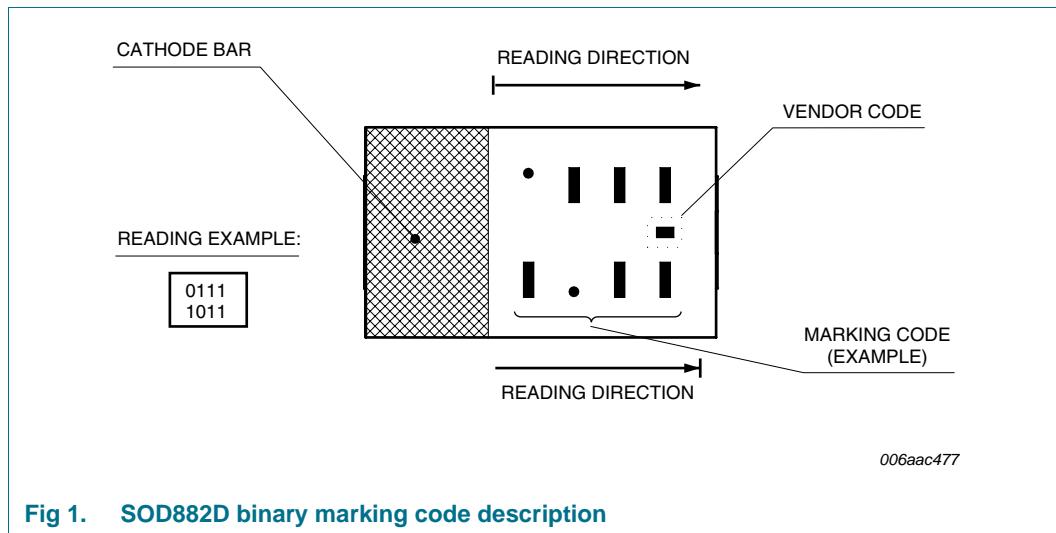
5. Limiting values

Table 5.   Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per diode						
P_{PP}	peak pulse power	$t_p = 8/20 \ \mu s$	[1]	-	130	W
I_{PP}	peak pulse current	$t_p = 8/20 \ \mu s$	[1]	-	12	A
T_j	junction temperature			-	150	°C
T_{amb}	ambient temperature			−55	+150	°C
T_{stg}	storage temperature			−65	+150	°C

[1]   Non-repetitive current pulse 8/20 μs exponential decay waveform according to IEC 61000-4-5.

Table 6.   ESD maximum ratings

$T_{amb} = 25 \ °C$ *unless otherwise specified.*

Symbol	Parameter	Conditions		Min	Max	Unit
V_{ESD}	electrostatic discharge voltage	IEC 61000-4-2 (contact discharge)	[1][2]	-	30	kV
		MIL-STD-883 (human body model)		-	10	kV

[1]   Device stressed with ten non-repetitive ESD pulses.

[2]   Measured from pin 1 to pin 2.

Table 7.   ESD standards compliance

Standard	Conditions
IEC 61000-4-2; level 4 (ESD)	> 15 kV (air); > 8 kV (contact)
MIL-STD-883; class 3 (human body model)	> 4 kV

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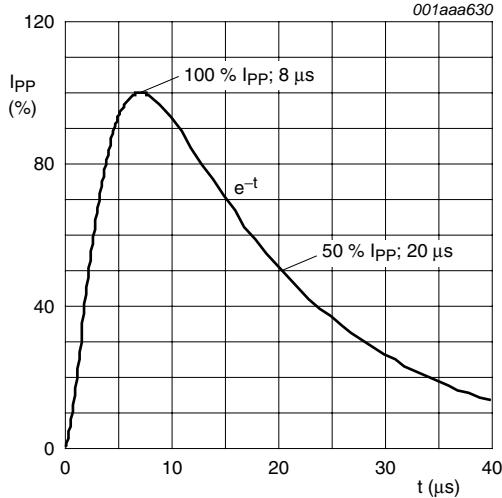
**Fig 2.**   **8/20 μs pulse waveform according to IEC 61000-4-5**
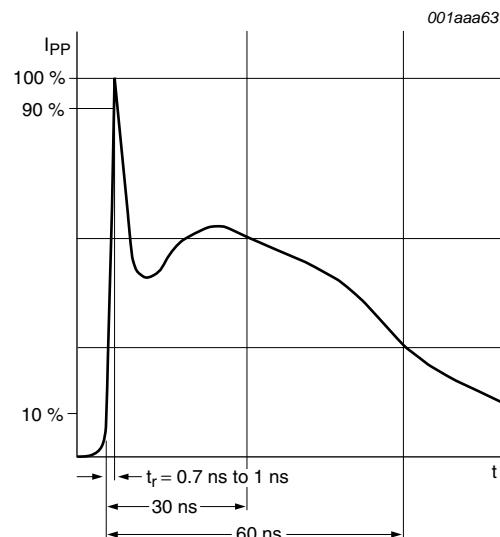
Fig 3.   **ESD pulse waveform according to IEC 61000-4-2**

6. Characteristics

Table 8.   Characteristics

T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Per diode						
V_{RWM}	reverse standoff voltage		-	-	5.0	V
I_{RM}	reverse leakage current	V_{RWM} = 5.0 V	-	5	100	nA
V_{BR}	breakdown voltage	I_R = 1 mA	5.5	-	9.5	V
C_d	diode capacitance	f = 1 MHz; V_R = 0 V	-	35	45	pF
V_{CL}	clamping voltage	[1][2]				
		I_{PP} = 1 A	-	-	10	V
		I_{PP} = 12 A	-	-	14	V
r_{dyn}	dynamic resistance	[2][3]				
		I_R = 10 A	-	0.1	-	Ω
		I_R = −10 A	-	0.15	-	Ω

[1]   Non-repetitive current pulse 8/20 μs exponential decay waveform according to IEC 61000-4-5.

[2]   Measured from pin 1 to pin 2.

[3]   Non-repetitive current pulse; Transmission Line Pulse (TLP) t_p = 100 ns; square pulse; ANSI/ESD STM5.1-2008.
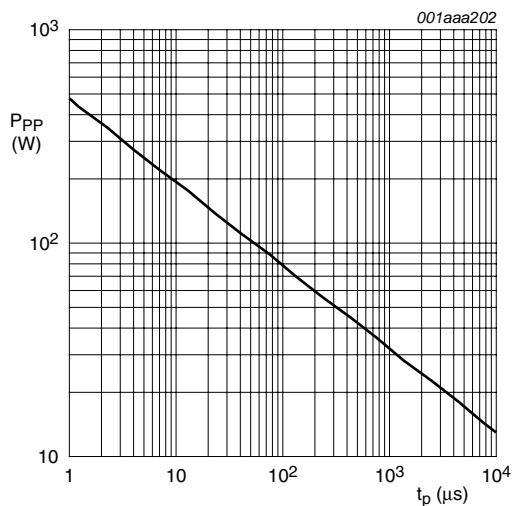
$T_{amb} = 25\ °C$

Fig 4. **Peak pulse power as a function of exponential pulse duration; typical values**
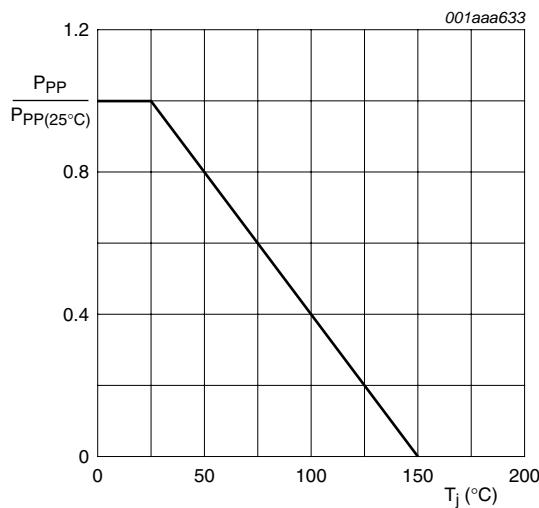
Fig 5. **Relative variation of peak pulse power as a function of junction temperature; typical values**
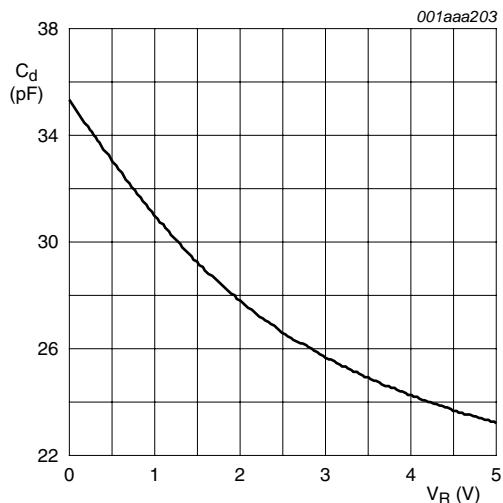
$f = 1\ MHz;\ T_{amb} = 25\ °C$

**Fig 6.** **Diode capacitance as a function of reverse voltage; typical values**
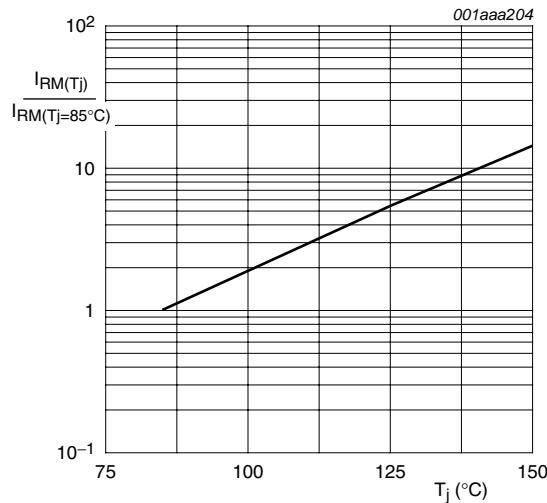
Fig 7. **Relative variation of reverse leakage current as a function of junction temperature; typical values**

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006aaa676
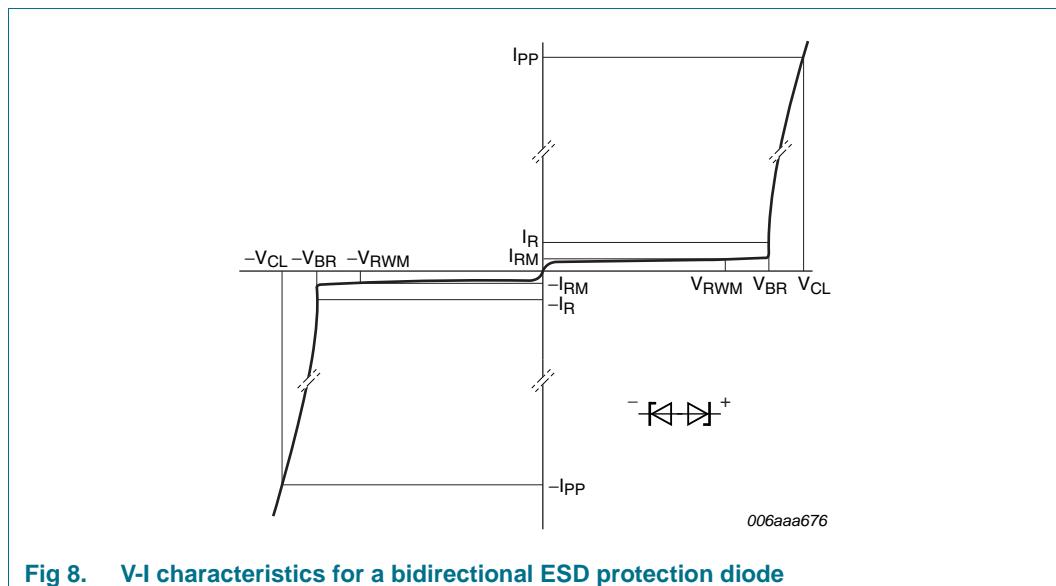
Fig 8.   **V-I characteristics for a bidirectional ESD protection diode**

ESD TESTER

R$_Z$

C$_Z$

IEC 61000-4-2 network
C$_Z$ = 150 pF; R$_Z$ = 330 Ω

DUT
(DEVICE
UNDER
TEST)

450 Ω

RG 223/U
50 Ω coax

10×
ATTENUATOR

4 GHz DIGITAL
OSCILLOSCOPE

50 Ω

vertical scale = 2 kV/div
horizontal scale = 15 ns/div

GND

unclamped +8 kV ESD pulse waveform
(IEC 61000-4-2 network)

vertical scale = 10 V/div
horizontal scale = 10 ns/div

GND

clamped +8 kV ESD pulse waveform
(IEC 61000-4-2 network) pin 1 to 2

vertical scale = 2 kV/div
horizontal scale = 15 ns/div

GND

unclamped −8 kV ESD pulse waveform
(IEC 61000-4-2 network)

GND

clamped −8 kV ESD pulse waveform
(IEC 61000-4-2 network) pin 1 to 2

vertical scale = 10 V/div
horizontal scale = 10 ns/div

006aac493

Fig 9.   ESD clamping test setup and waveforms

7. Application information

The PESD5V0S1BLD is designed for the protection of one bidirectional data or signal line from the damage caused by ESD and surge pulses. The device may be used on lines where the signal polarities are both, positive and negative with respect to ground. The PESD5V0S1BLD provides a surge capability of 130 W per line for an 8/20 µs waveform.
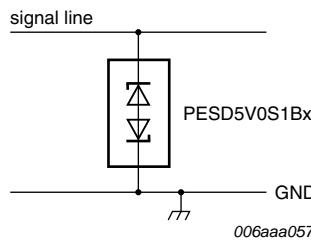
Fig 10. Application diagram

Circuit board layout and protection device placement

Circuit board layout is critical for the suppression of ESD, Electrical Fast Transient (EFT) and surge transients. The following guidelines are recommended:

1. Place the device as close to the input terminal or connector as possible.
2. The path length between the device and the protected line should be minimized.
3. Keep parallel signal paths to a minimum.
4. Avoid running protected conductors in parallel with unprotected conductors.
5. Minimize all Printed-Circuit Board (PCB) conductive loops including power and ground loops.
6. Minimize the length of the transient return path to ground.
7. Avoid using shared transient return paths to a common ground point.
8. Ground planes should be used whenever possible. For multilayer PCBs, use ground vias.

8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline

Dimensions in mm

10-08-06
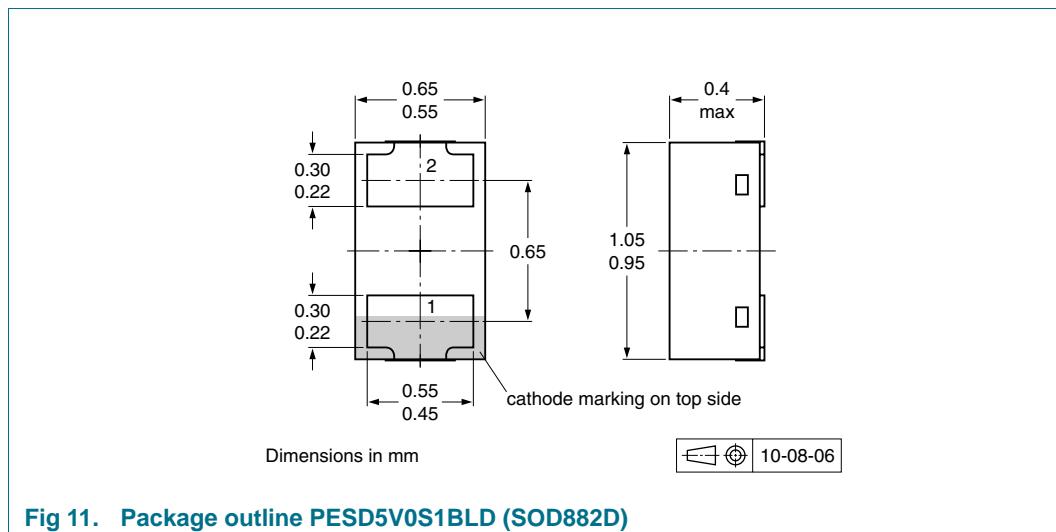
Fig 11. Package outline PESD5V0S1BLD (SOD882D)

10. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity
			10000
PESD5V0S1BLD	SOD882D	2 mm pitch, 8 mm tape and reel	-315

[1] For further information and the availability of packing methods, see Section 14.

11. Soldering

solder lands

solder resist

solder paste

Dimensions in mm
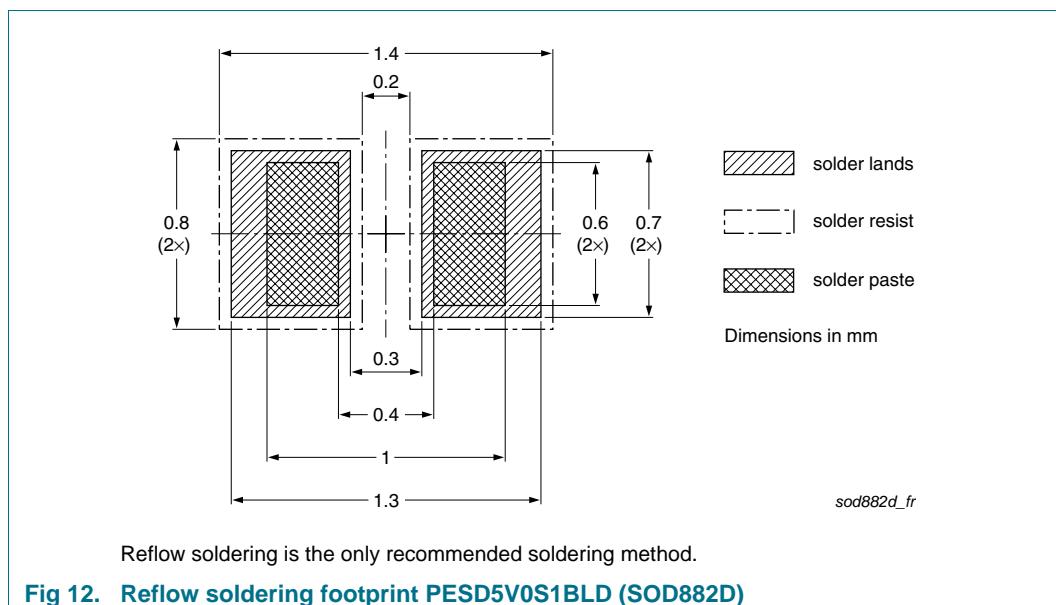
sod882d_fr

Reflow soldering is the only recommended soldering method.

Fig 12. Reflow soldering footprint PESD5V0S1BLD (SOD882D)

12. Revision history

Table 10.   Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PESD5V0S1BLD v.1	20101012	Product data sheet	-	-

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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